## PRELIMINARY DATA SHEET



# N-CHANNEL GaAs MES FET NE650103M

## 10 W L, S-BAND POWER GaAs MES FET

#### **DESCRIPTION**

The NE650103M is a 10 W GaAs MES FET designed for power transmitter applications for mobile communication base station systems. It is capable of delivering 10 W of output power (CW) with high linear gain, high efficiency and excellent distortion.

Reliability and performance uniformity are assured by our stringent quality and control procedures.

#### **FEATURES**

- High output power: Po (1 dB) = 40.0 dBm TYP.
- High linear gain: G<sub>L</sub> = 11.0 dB TYP.
- High power added efficiency: η<sub>add</sub> = 45% TYP. @ Vps = 10.0 V, I<sub>Dset</sub> = 1.5 A (RF OFF), f = 2.3 GHz

### ORDERING INFORMATION

Part Number	Package	Supplying Form
NE650103M	3M (T-91M)	ESD Protective tray.

**Remark** To order evaluation samples, contact your nearby sales office. The unit sample quantity is 1 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.



## ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	Vos	15	V
Gate to Drain Voltage	V <sub>GD</sub>	-18	٧
Gate to Source Voltage	Vgso	-7	V
Drain Current	lο	5	А
Gate Current	lg	45	mA
Total Power Dissipation	Ptot	33	W
Channel Temperature	Tch	175	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C

## **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>		_	10.0	10.0	V
Gain Compression	Gcomp		-		3.0	dB
Channel Temperature	Tch		-	-	+150	°C
Gate Resistance	Rg		-	_	100	Ω

## **ELECTRICAL CHARACTERISTICS**

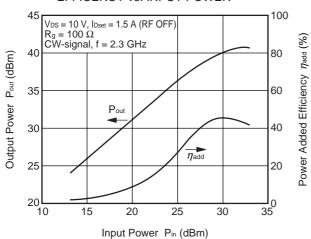
(TA = +25°C, unless otherwise specified, using our standard test fixture.)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Saturated Drain Current	Ipss	V <sub>DS</sub> = 1.5 V, V <sub>GS</sub> = 0 V	2.0	5.0	7.0	Α
Pinch-off Voltage	Vp	V <sub>DS</sub> = 2.5 V, I <sub>D</sub> = 23 mA	-4.0	-2.5	-1.0	V
Thermal Resistance	Rth	Channel to Case	_	4.0	4.5	°C/W
Gain 1 dB Compression Output Power	Po (1 dB)	f = 2.3 GHz, Vps = 10.0 V,	39.0	40.0	-	dBm
Power Added Efficiency	$\eta$ add	$R_g = 100 \Omega$ , $I_{Dset} \le 1.5 A$ (RF OFF)	_	45	-	%
Linear Gain Note	GL		10.0	11.0	-	dB

Note  $P_{in} \le 23 dBm$ 

### TYPICAL CHARACTERISTICS (TA = +25°C)

## OUTPUT POWER, POWER ADDED EFFICENCY vs. INPUT POWER



**Remark** The graph indicates nominal characteristics.

#### **S-PARAMETERS**

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

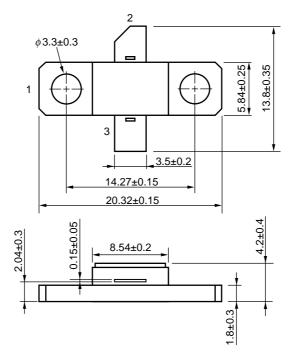
Click here to download S-parameters.

 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$ 

URL http://www.csd-nec.com/

## PACKAGE DIMENSIONS

3M (T-91M) (UNIT: mm)



## **PIN CONNECTIONS**

- 1. Source
- 2. Gate
- 3. Drain



### RECOMMENDED MOUNTING CONDITIONS FOR CORRECT USE

- (1) Fix to a heat sink or mount surface completely with screws at the two holes of the flange.
- (2) The recommended torque strength of the screws is 29.4 N·cm typical using M3 type screws.
- (3) The recommended flatness of the mount surface is less than  $\pm 10~\mu m$  (roughness of surface is  $\nabla \nabla \nabla$ ).

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol	
Partial Heating	Peak temperature (pin temperature) Soldering time (per pin of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).

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- The information in this document is current as of May, 2003. The information is subject to change
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  - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
  - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

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NEC NE650103M

#### Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
- Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

#### ▶ For further information, please contact

#### NEC Compound Semiconductor Devices, Ltd.

5th Sales Group, Sales Division TEL: +81-44-435-1588 FAX: +81-44-435-1579 E-mail: salesinfo@csd-nec.com

#### **NEC Compound Semiconductor Devices Hong Kong Limited**

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309 E-mail: ncsd-hk@elhk.nec.com.hk

Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859 Korea Branch Office TEL: +82-2-558-2120 FAX: +82-2-558-5209

#### NEC Electronics (Europe) GmbH http://www.ee.nec.de/

TEL: +49-211-6503-01 FAX: +49-211-6503-487

## California Eastern Laboratories, Inc. http://www.cel.com/

TEL: +1-408-988-3500 FAX: +1-408-988-0279